

TC74HC07AP, TC74HC07AF

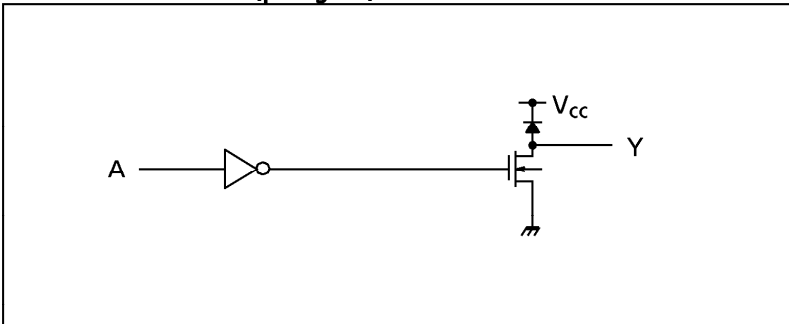
HEX BUFFER (OPEN DRAIN)

The TC74HC07A is a high speed CMOS BUFFER fabricated with silicon gate C2MOS technology. It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. Pin configuration and function are the same as the TC74HCT7007A. But the TC74HC07A has high performance MOS N - channel transistor (OPEN - DRAIN) outputs. This device can, therefore, with a suitable pull - up resistors, be used in wired - AND, LED driver and other applications. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

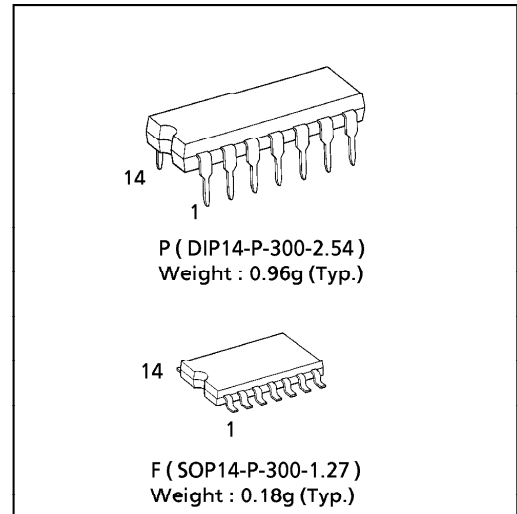
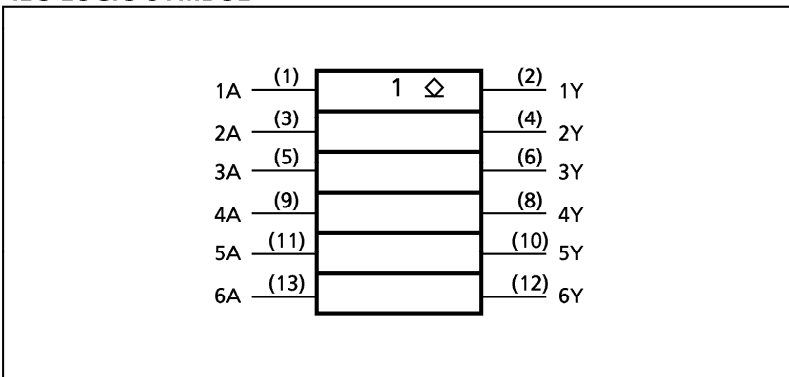
FEATURES :

- High Speed..... $t_{pz} = 5\text{ns}(\text{typ.})$ at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 1\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC} (\text{Min.})$
- Output Drive Capability..... 10 LSTTL Loads
- Wide Operating Voltage Range.... $V_{CC} (\text{opr.}) = 2\text{V} \sim 6\text{V}$
- Open Drain Structure.
- Pin and Function Compatible with 74LS07

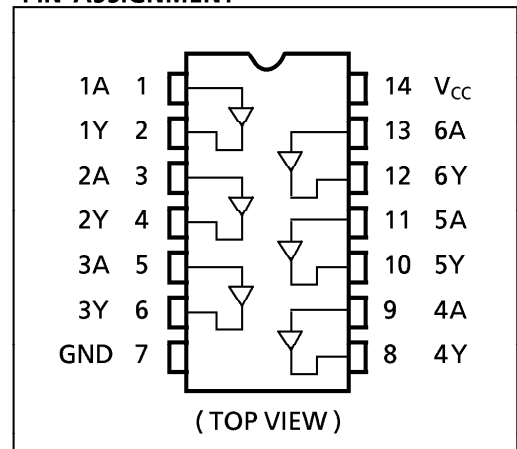
SYSTEM DIAGRAM (per gate)



IEC LOGIC SYMBOL



PIN ASSIGNMENT



TRUTH TABLE

A	Y
L	L
H	Z

Z : High Impedance

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} / Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	-65~150	°C

*500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$. From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2~6	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	t_r, t_f	0~1000 ($V_{CC} = 2.0\text{V}$) 0~500 ($V_{CC} = 4.5\text{V}$) 0~400 ($V_{CC} = 6.0\text{V}$)	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT		
				MIN.	TYP.	MAX.	MIN.	MAX.			
High - Level Input Voltage	V_{IH}		2.0 4.5 6.0	1.50 3.15 4.20	— — —	— — —	1.50 3.15 4.20	— — —	V		
Low - Level Input Voltage	V_{IL}		2.0 4.5 6.0	— — —	— — —	0.50 1.35 1.80	— — —	0.50 1.35 1.80	V		
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}		$I_{OL} = 20\mu\text{A}$	2.0	—	0.0	0.1	—	0.1	V
					4.5	—	0.0	0.1	—	0.1	
					6.0	—	0.0	0.1	—	0.1	
					4.5	—	0.17	0.26	—	0.33	
					6.0	—	0.18	0.26	—	0.33	
Output Off - State Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$	6.0	—	—	± 0.5	—	± 5.0	μA		
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	± 0.1	—	± 1.0	μA		
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	1.0	—	10.0	μA		

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t_{THL}		—	4	8	ns
Propagation Delay Time	t_{pLZ}	$R_L = 1\text{k}\Omega$	—	5	15	
Propagation Delay Time	t_{pZL}	$R_L = 1\text{k}\Omega$	—	5	15	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40\sim 85^\circ\text{C}$		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t_{THL}		2.0	—	30	75	—	95	ns
			4.5	—	8	15	—	19	
			6.0	—	7	13	—	16	
Propagation Delay Time	t_{pLZ}	$R_L = 1\text{k}\Omega$	2.0	—	10	90	—	115	
			4.5	—	7	18	—	23	
			6.0	—	6	15	—	20	
Propagation Delay Time	t_{pZL}	$R_L = 1\text{k}\Omega$	2.0	—	17	90	—	115	
			4.5	—	7	18	—	23	
			6.0	—	5	15	—	20	
Input Capacitance	C_{IN}			—	5	10	—	10	pF
Output Capacitance	C_{OUT}			—	3	—	—	—	
Power Dissipation Capacitance	$C_{PD} (1)$			—	4	—	—	—	

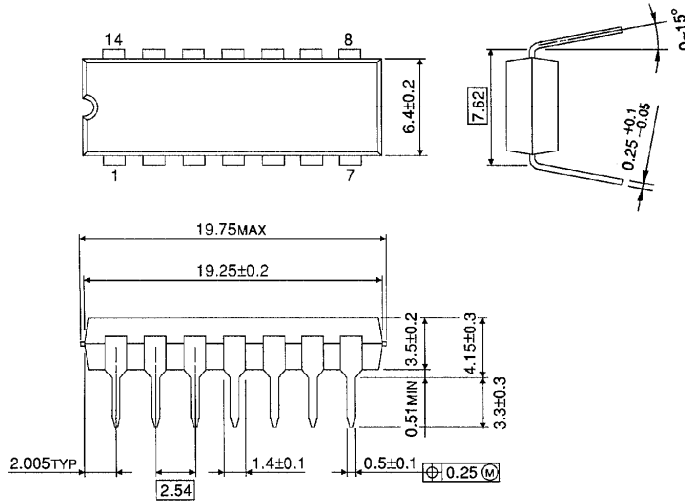
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 \text{ (per Gate)}$$

DIP 14PIN OUTLINE DRAWING (DIP14-P-300-2.54)

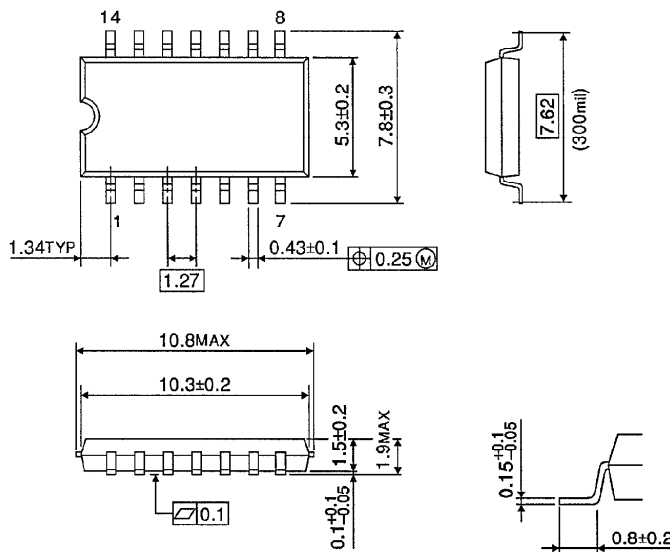
Unit in mm



Weight : 0.96g (Typ.)

SOP 14PIN (200mil BODY) OUTLINE DRAWING (SOP14-P-300-1.27)

Unit in mm



Weight : 0.18g (Typ.)